

Commissioner of Patents and Trademarks Washington, D.C. 20231

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Subject: .

Serial No. 09/863,224 05/24/01

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METHOD TO SOLVE VIA POISONING FOR POROUS LOW-K DIELECTRIC

Grp. Art Unit: 2812

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

- U.S. Patent 5,916,823 to Lou et al., "Method for Making Dual Damascene Contact," describes a method for forming a dual damascene structure with a low-k dielectric material.
- U.S. Patent 6,074,942 to Lou, "Method for Forming a Dual Damascene Contact and Interconnect," describes a method of forming a dual damascene structure.

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U.S. Patent 6,140,220 to Lin, "Dual Damascene Process and Structure with Dielectric Barrier Layer," describes a dual damascene structure with a dielectric layer, and process for manufacturing it.

Sincerely,

George O. Saile Reg. No. 19572